

isc Silicon NPN Power Transistor

2SC3910

DESCRIPTION

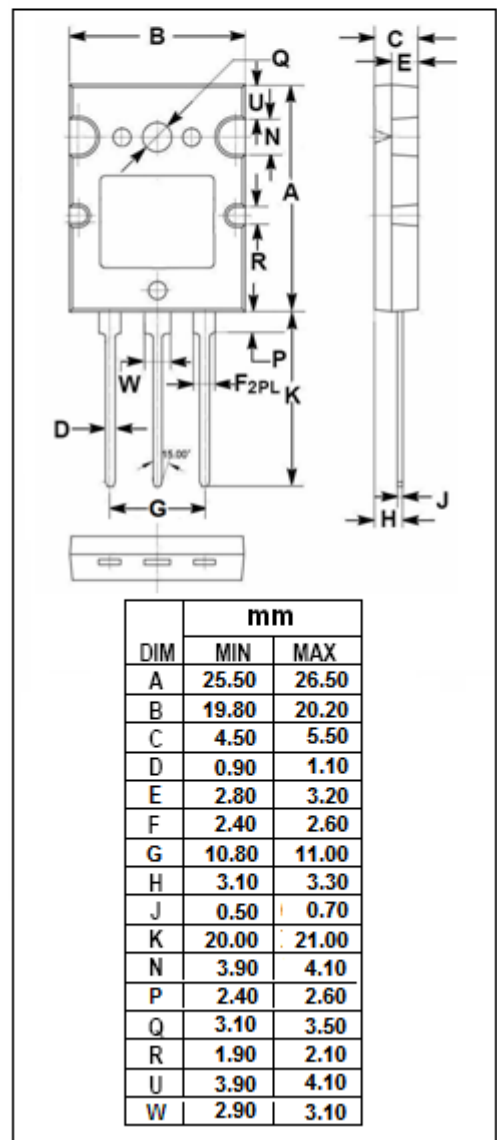
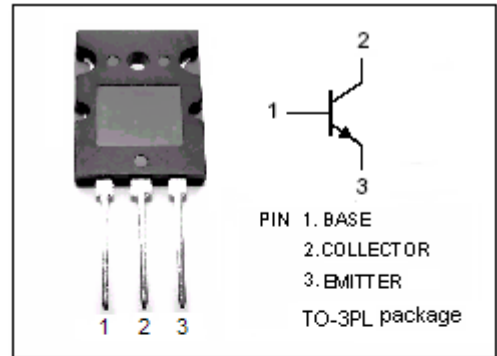
- High Speed Switching
- High Collector-Base Breakdown Voltage-
: $V_{(BR)CEO} = 800V(\text{Min})$
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for high speed switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	500	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	150	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3.5	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.5\text{A}; L=25\text{mH}$	500			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=8.0\text{A}; I_B=1.6\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8.0\text{A}; I_B=1.6\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	15			
h_{FE-2}	DC Current Gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	10			
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=10\text{V}; f=0.5\text{MHz}$		2		MHz

Switching times

t_{on}	Turn-on Time	$I_C=8\text{A}; I_{B1}=1.6\text{A}; I_{B2}=-1.6\text{A}; V_{CC}=200\text{V}$			1.0	μs
t_{stg}	Storage Time				3.0	μs
t_f	Fall Time				1.0	μs